

	Type	Hits	Search Text	DBs	Time Stamp	C	o	r	E
						o	m	d	r
						m	e	n	e
						s	n	s	r
									s
1	BRS	127	sonos with flash near memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:42				0
2	BRS	40	sonos with flash near memory and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:29				0
3	BRS	19	sonos with flash near memory and spacer and tunnel\$ with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:29				0
4	BRS	16	sonos with flash near memory and spacer and tunnel\$ with nitride and isolat\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:30				0
5	BRS	9	sonos with flash near memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 14:56				0
6	BRS	16	sonos with flash near memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:41				0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
7	BRS	2	sonos with flash near memory and (two or double) with nitride with tunnel\$ or (monos or sonos) with flash near memory and (two or double or dual or separat\$) with nitride with tunnel\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:44		0
8	BRS	4	(monos or sonos) with flash near memory and (two or double or dual or separat\$) with nitride with tunnel\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/03 16:45		0
9	BRS	4	(monos or sonos) with flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 17:41		0
10	BRS	309	flash near memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:48		0
11	BRS	31	flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:39		0

	Type	Hits	Search Text	DBs	Time Stamp	Command s	Error s	Error s
12	BRS	43	memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:38			0
13	BRS	42	(memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon) not (US-2004015743 4-A1.DID. and (flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:39			0
14	BRS	31	flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:39			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
15	BRS	12	(memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon) not (flash near memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:39		0
16	BRS	1	memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon and ono with sacrificial and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:49		0
17	BRS	1	memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon and ono with sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:50		0

	Type	Hits	Search Text	DBs	Time Stamp	Command	Errors
18	BRS	72	memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 18:52		0
19	BRS	67	sacrificial (memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon and sacrificial) not (memory and (two or double or dual or separat\$ or divid\$) with nitride with tunnel\$ and spacer and polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 19:06		0
20	IS& R	2	("6596609").PN .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 19:08		0
21	IS& R	3	("6218224").PN .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 19:09		0
22	IS& R	2	("6103563").PN .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 19:09		0
23	IS& R	2	("5087583").PN .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/04 19:09		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
24	BRS	51	memory and spacer and tunnel\$ with nitride and isolat\$ and polysilicon with oxide and ono and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:01		0
25	BRS	1	spacer and (split\$ or dual or double) with tunnel\$ with nitride and isolat\$ and polysilicon with oxide and ono and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:03		0
26	BRS	7	spacer and (split\$ or dual or double or two) with tunnel\$ with nitride and polysilicon with oxide and sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:06		0
27	BRS	47	spacer and (split\$ or dual or double or two) with tunnel\$ with nitride and polysilicon with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:11		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
28	BRS	1	spacer and (split\$ or dual or double or two) near tunnel\$ near nitride and polysilicon and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:13		0
29	BRS	1	spacer and (split\$ or dual or double or two) near tunnel\$ near nitride and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:13		0
30	BRS	1	(split\$ or dual or double or two) near tunnel\$ near nitride and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:13		0
31	BRS	1	(split\$ or dual or double or two or both) near tunnel\$ near nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:14		0
32	BRS	11	(split\$ or dual or double or two or both) with tunnel\$ near nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:17		0
33	BRS	24 2	(split\$ or dual or double or two or both) with tunnel\$ with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:18		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
34	BRS	131	(etch\$ or via or hole or opening) with tunnel\$ with nitride same (fill\$ or deposit\$) with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:21		0
35	BRS	332	(etch\$ or via or hole or opening) with tunnel\$ with nitride same (fill\$ or deposit\$ or form\$4) with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:23		0
36	BRS	35	(etch\$ or via or hole or opening) with tunnel\$ with nitride same (fill\$ or deposit\$ or form\$4) with oxide and (sonos or monos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:36		0
37	BRS	129	(etch\$ or via or hole or opening) with tunnel\$ with nitride same (fill\$ or deposit\$ or form\$4) with oxide and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:37		0
38	BRS	1	2002-477652.NR AN.	DERWENT	2004/09/10 16:21		0